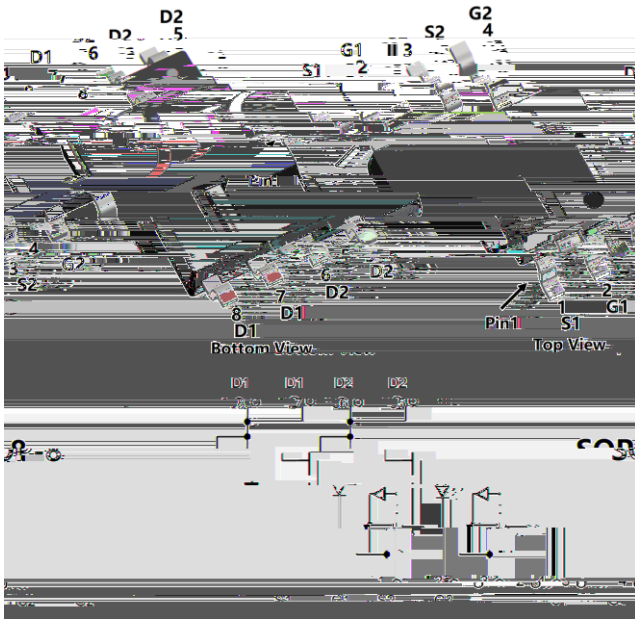




**P-Channel and P-Channel Complementary**



**Product Summary**

- V<sub>DS</sub>
- I<sub>D</sub>
- R<sub>DS(ON)</sub>( at V<sub>GS</sub>=-10V)
- R<sub>DS(ON)</sub>( at V<sub>GS</sub>=-4.5V)
- 100% EAS Tested

**General Description**

- Trench Power LV MOSFET
- High density cell design
- High Speed switching
- Moisture Sensitivity
- Epoxy Meets UL 94
- Halogen Free

**Applications**

- Battery protection
- Load switch
- Power management

**Absolute Maximum Ratings** (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol			
Drain-source Voltage	V <sub>DS</sub>			
Gate-source Voltage	V <sub>GS</sub>	±20	V	
Drain Current (Pulse) T <sub>A</sub> =25°C	I <sub>D</sub>	-10	A	



# YJS7328B

## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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Static Parameter



Typical Electrical and Thermal Characteristics Diagrams

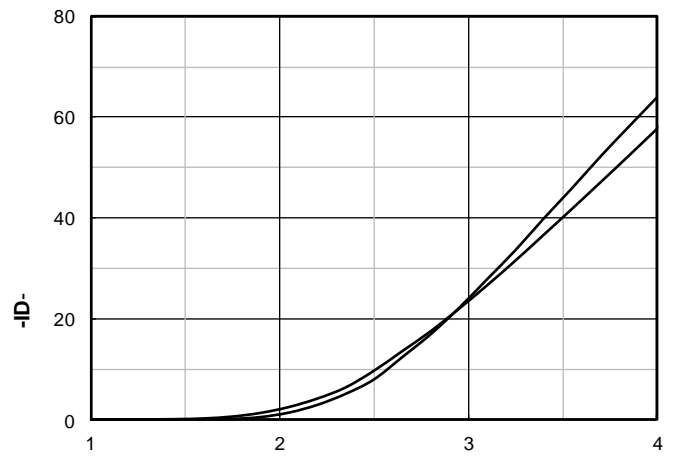
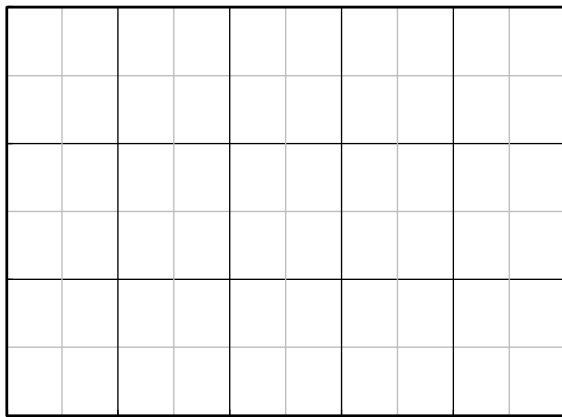


Figure 1. Output Characteristics



# YJS7328B

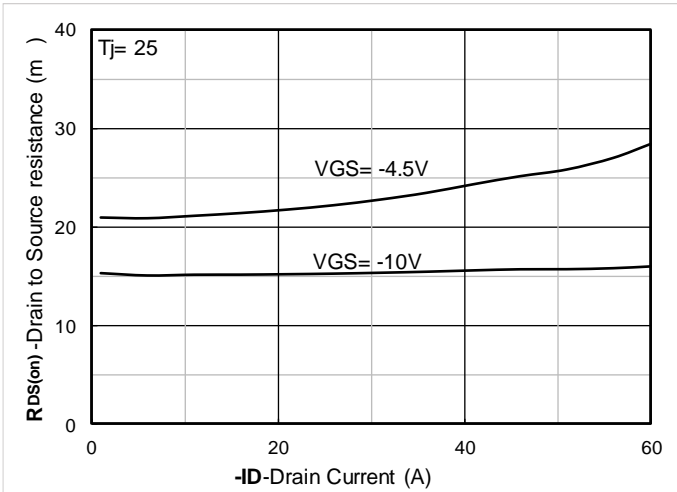


Figure 7.  $R_{DS(on)}$  VS Drain Current

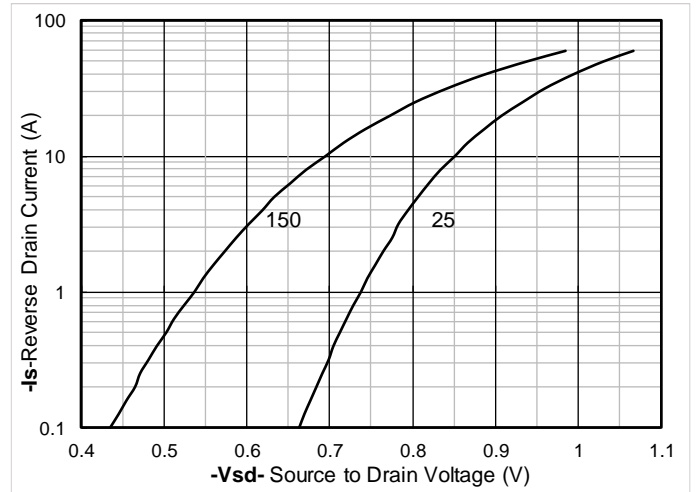


Figure 8. Forward characteristics of reverse diode

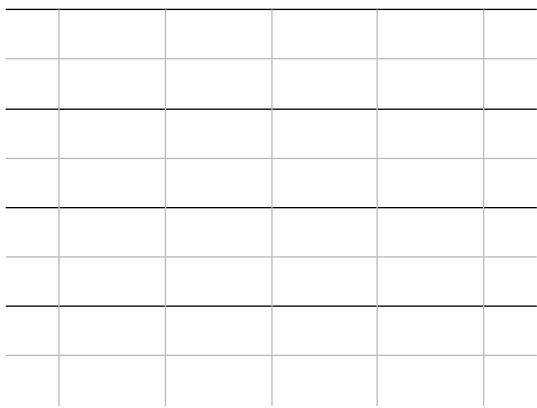


Figure 9. Normalized breakdown voltage

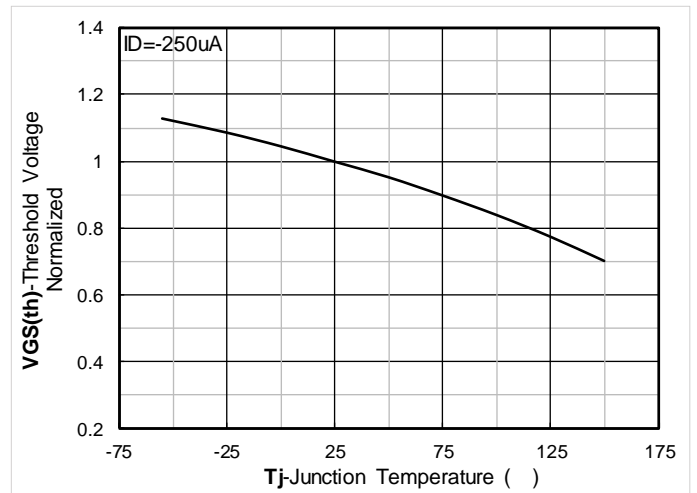
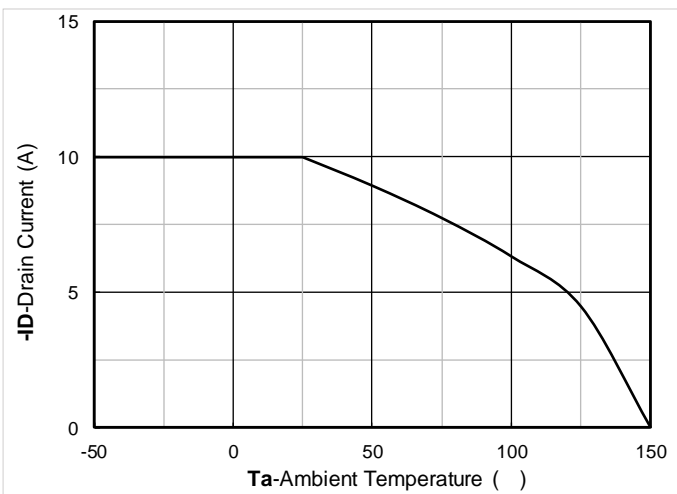
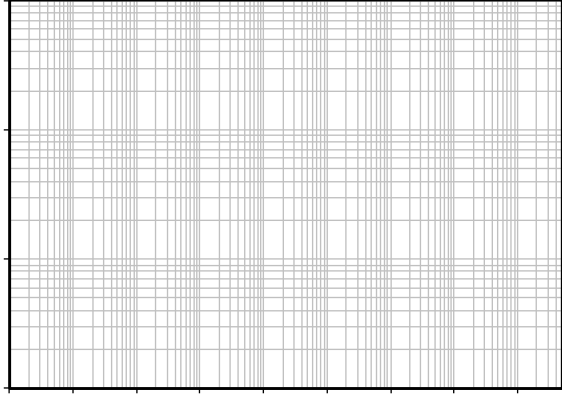


Figure 10. Normalized Threshold voltage







SOP-8 Package information

